

Momentum-resolved TDDFT Algorithm for Real Time Tracking of Electronic Excitation

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Ultrafast electronic dynamics in solids lies at the core of modern condensed matter and materials physics. To build up a practical *ab initio* method in this field, we develop the momentum-resolved real-time time dependent density functional theory (rt-TDDFT), together with the implementation of length gauge electromagnetic field. When applied to simulate elementary excitation in graphene, different excitation modes, only distinguishable in momentum space, are observed. The momentum-resolved rt-TDDFT is important and efficient for the study of ultrafast dynamics in extended systems.

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I. INTRODUCTION

Real-time (rt) time dependent density functional theory (TDDFT) is an efficient *ab initio* method to study electronic dynamics in complex electron-nuclear systems, especially for those in the electronically excited states. Compared with other widely used approaches such as frequency domain TDDFT, quasi-particle GW and Bethe-Salpeter equations, rt-TDDFT has two major advantages: (i) Time-dependent Kohn-Sham (TDKS) equations in rt-TDDFT include all nonlinear effects and are intrinsically non-perturbative, making rt-TDDFT a better tool to describe materials in strong field; (ii) rt-TDDFT directly provides real time evolution of electronic wavefunctions together with ionic movements, presenting a unique way for the real-time tracking of ultrafast dynamics and phenomena far from equilibrium. Thus, rt-TDDFT is a natural choice for the exploration of strong field physics and ultrafast phenomena. Motivated by the rapid developments in above fields, rt-TDDFT is drawing more and more attentions.

Nevertheless, rt-TDDFT is not widely used as the method of choice in literature, being much less popular than other density functional theory (DFT) based approaches such as Δ SCF, DFT+U, frequency-domain TDDFT, etc. The major reasons responsible for this fact is the limited functionality in most rt-TDDFT approaches and challenging computational consumption. Most previous rt-TDDFT investigations focus on the photoabsorption and related properties of finite size zero-dimensional (0D) systems (atoms/molecules/nanoparticles) including the strong field optical spectra [1–23], photochemical stability [24–28], and recently plasmonic excitations [29–38]. In 0D systems, only single Γ point is needed in the reciprocal space sampling. Thus, Γ -only algorithm is overwhelm-

ingly common implemented and used in rt-TDDFT simulations. However, to study photoexcitation and electronic dynamics in extended systems, Γ -only is insufficient and momentum-resolved ($\mathbf{k}$ -resolved) sampling in the reciprocal space is needed.

Another advantages of using $\mathbf{k}$ -resolved rt-TDDFT is computational efficiency. With Γ -only TDDFT, to get the accurate charge density and ionic forces, an extraordinary large supercell has to be invoked. Many previous studies on extended systems belong to this scenario [39–47], including our recent works about ultrafast electron-hole dynamics in dye-sensitized solar cells [48–53] and nonthermal melting of silicon [54]. Using $\mathbf{k}$ -resolved algorithms, and at the same accuracy level, the supercell size as well as the computational cost, can be largely reduced.

Besides technical advantages, $\mathbf{k}$ -resolved algorithm introduces the important $\mathbf{k}$ -space resolution and a new degree of freedom, which is essential to describe key quantities and important physics in condensed matter and materials such as band structures, quasiparticles, and valley dynamics. Only rt-TDDFT with $\mathbf{k}$ -resolved sampling can provide essential information concerning their real time evolution.

In literature $\mathbf{k}$ -resolved rt-TDDFT algorithms have been implemented by several groups [55–58] and applied for both semiconductors [59–67] and metals [68, 69]. These implementations employ either real space grids or all-electron full-potential linearized augmented-planewaves as basis sets. On the other hand, numerical atomic orbitals (NAO) have been an common choice to dramatically reduce computation cost for complex systems, and have been widely used in DFT codes. The biggest advantage of using NAO is the extremely small computational cost. To describe a system with N_a atoms, only about $10 \times N_a$ NAOs are required, while 10^3 to $10^4 \times N_a$ real space grids or plane waves have to be used. In addition, with a relatively small real-space cut-off for NAOs, the order- N linear scaling with respect to system size can be achieved. Since a major difficulty

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in developing rt-TDDFT is its extreme time consumption due to the use of ultrasmall time step (on the order of ~ 1 attosecond), NAO based $\mathbf{k}$ -resolved rt-TDDFT is very promising for simulating more realistic complex condensed matter materials and interfaces with a longer simulation time. However, to take the advantages of NAOs, new and more complicated framework and implementation in rt-TDDFT is unavoidable.

In this work we stride to tackle above major challenges in rt-TDDFT. We have developed the $\mathbf{k}$ -resolved rt-TDDFT algorithm based on local basis sets using numerical atomic orbitals. This approach enables rt-TDDFT calculations of solids and surfaces using a small unit cell, reducing computational cost by several order of magnitudes ($1/100$). Moreover, momentum-resolved excitation dynamics in model systems are observed. For instance, $\mathbf{k}$ selective photoexcitation in graphene has been observed, where three distinct photoexcitation modes located at different $\mathbf{k}$ were induced upon laser illumination. This kind of $\mathbf{k}$ dependent electronic dynamics are ubiquitous in solids. Therefore, we expect highly efficient $\mathbf{k}$ -resolved rt-TDDFT algorithms employing local bases is an important development and will be widely used in ultrafast research and optimal control of quantum materials.

II. METHODOLOGY

The main framework of $\mathbf{k}$ -resolved rt-TDDFT algorithm is inherited from an earlier single- Γ version of Time Dependent *ab initio* Package (TDAP) [70], which is based on the SIESTA [71, 72] package. In such a rt-TDDFT algorithm, the flowchart of a given ionic step is shown in Fig. 1. Each process is described in detail in the following sections, marked with the same labels as in Fig. 1. Atomic units $\hbar = m_e = e = 1$ are used throughout this work.

A. Hamiltonian and Overlap Matrix

Occupying the periodical boundary condition, the lattice vectors are denoted as $\mathbf{R}_s$ ($s = 1, 2, 3 \dots N$) and the atoms i in the unit cell located at positions $\mathbf{b}_i$, where N is truncated to a finite supercell. A set of numerical atomic-centered orbitals (NAOs) $\{\xi_{i\alpha}\}$ is associated with each atom, where α denotes both the orbital and angular quantum numbers of the atomic state, together with the multiple radial basis function ζ [71]. Here, since all the operators and functions are time-dependent, we only denote the explicit dependence on t as $f(t)$ and omit t for the implicit dependence.

Overlap matrix $S_{\mathbf{k}}$ and Hamiltonian $H_{\mathbf{k}}$ at the each $\mathbf{k}$ point are expressed with NAOs:

$$S_{i\alpha,j\beta,\mathbf{k}} = \sum_s e^{-i\mathbf{k}\cdot\mathbf{R}_s} \langle \xi_{i\alpha}(\mathbf{r} + \mathbf{R}_s + \mathbf{b}_i) | \xi_{j\beta}(\mathbf{r} + \mathbf{b}_j) \rangle, \quad (1)$$

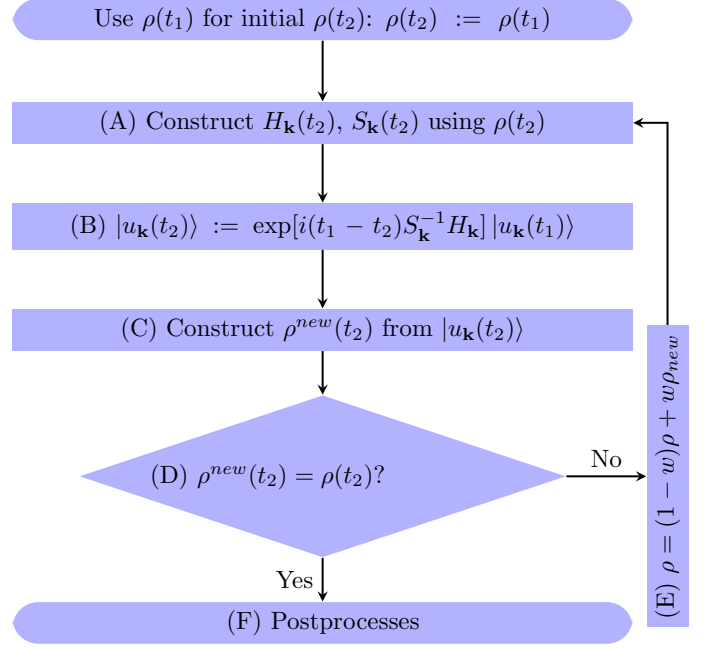


FIG. 1. Flowchart of $\mathbf{k}$ -resolved algorithm.

$$H_{i\alpha,j\beta,\mathbf{k}} = \sum_s e^{-i\mathbf{k}\cdot\mathbf{R}_s} \langle \xi_{i\alpha}(\mathbf{r} + \mathbf{R}_s + \mathbf{b}_i) | \hat{H} | \xi_{j\beta}(\mathbf{r} + \mathbf{b}_j) \rangle \quad (2)$$

where

$$\hat{H} = \hat{T} + \sum V_I^{local}(\mathbf{r}) + \sum V_I^{KB} + V^H(\mathbf{r}) + V^{XC}(\mathbf{r}) + V^{ext}(\mathbf{r}) \quad (3)$$

is the Hamiltonian operator, where $\hat{T} = \frac{1}{2}\nabla_{\mathbf{r}}^2$ is the kinetic energy operator, I is the atom index, V_I^{local} and V_I^{KB} are the local and Kleinman-Bylander parts of the pseudopotential of atom I , V^H is the Hartree potential, V^{XC} is the exchange-correlation (XC) potential and V^{Ext} is the potential of external electric field. Details in the calculation of $\langle \xi_{i\alpha}(\mathbf{r} + \mathbf{R}_s + \mathbf{b}_i) | \hat{H} | \xi_{j\beta}(\mathbf{r} + \mathbf{b}_j) \rangle$ are described in Ref. [72]. Occupying adiabatic LDA/GGA approximation [73], V^{XC} does not depend explicitly on time t , i.e. $V^{XC}[\rho(\mathbf{r}, t), t] = V^{XC}[\rho(\mathbf{r}, t)]$. Thus, most DFT XC functionals such as Perdew-Wang [74], Perdew-Burke-Ernzerhof [75], Becke-Lee-Yang-Parr [76, 77], and van der Waals density functional [78, 79] are compatible in our rt-TDDFT implementation.

To simulate a laser-material interaction, the time-dependent electric field $\mathbf{E}(t)$ is introduced to V^{ext} in length gauge as:

$$V^{ext}(\mathbf{r}, t) = -\mathbf{E}(t) \cdot \mathbf{r}. \quad (4)$$

Time dependent $\mathbf{E}(t)$ can be tuned as any shape in time. An example is a Gaussian wave package

$$\mathbf{E}(t) = \mathbf{E}_0 \cos(2\pi f t + \phi) \exp\left[-\frac{(t - t_0)^2}{2\sigma^2}\right] \quad (5)$$

where f is the frequency, t_0 is the peak time, and ϕ is the auxiliary phase.

We note that, the transitional symmetry of Hamiltonian is broken by finite $\mathbf{E}$, since

$$V^{ext}(\mathbf{r} + \mathbf{R}_s, t) = -\mathbf{E}(t) \cdot (\mathbf{r} + \mathbf{R}_s) \neq -\mathbf{E}(t) \cdot \mathbf{r}. \quad (6)$$

Thus, a common solution is using a sawtooth field along spatial direction $\mu \in x, y, z$

$$E_\mu(\mathbf{r}, t) = \begin{cases} E_\mu(t) & \epsilon < x_\mu < L_\mu - \epsilon, \\ -E_\mu(t)L_\mu/2\epsilon & -\epsilon < x_\mu < +\epsilon. \end{cases} \quad (7)$$

where L_μ is the length of unit cell along μ and $\epsilon \rightarrow 0$. Thus, $-E_\mu(t)L_\mu/2\epsilon \rightarrow \infty$, it requires that charge density vanishes $\rho(x_\mu) = 0$ in area $-\epsilon < x_\mu < +\epsilon$, otherwise the energy diverges. Thus, a vacuum layer is essential along μ . It limits the application of this method. Dynamical electric field in vector gauge removes the requirement of the vacuum layer. This method will be implemented and discussed in our following work.

B. Propagation

With TD Hamiltonian and overlap matrix, TDKS equation is solved to obtain $|u_{n\mathbf{k}}(\mathbf{r}, t)\rangle$ from the state $|u_{n\mathbf{k}}(\mathbf{r}, t)\rangle$ at the previous time step:

$$|u_{n\mathbf{k}}(\mathbf{r}, t_2)\rangle = \exp[-iS_{\mathbf{k}}^{-1}(t')H_{\mathbf{k}}(t')\Delta t] |u_{n\mathbf{k}}(\mathbf{r}, t_1)\rangle. \quad (8)$$

where $\Delta t = t_2 - t_1$ is the length of time step, $|u_{n\mathbf{k}}(\mathbf{r}, t)\rangle$ is Bloch function and $t' \approx (t_1 + t_2)/2$. It is difficult to evaluate $H_{\mathbf{k}}(t')$ and $S_{\mathbf{k}}(t')$ directly. Because Δt is quite small (< 0.05 fs), the ion positions barely changes from t_1 to t_2 . Since $S_{\mathbf{k}}(t)$ is only determined by ionic positions (Eq. (1)), it is accurate enough to occupy $S_{\mathbf{k}}(t') = S_{\mathbf{k}}(t_2)$. However, $H_{\mathbf{k}}(t)$ may largely change due to the rapid evolution of electrons. To approaching $H_{\mathbf{k}}(t')$, two options are available:

$$H_{\mathbf{k}}(t') = H_{\mathbf{k}}(t_2) \quad (9)$$

or

$$H_{\mathbf{k}}(t') = \frac{1}{2}H_{\mathbf{k}}(t_2) + \frac{1}{2}H_{\mathbf{k}}(t_1). \quad (10)$$

Eq 9 is more convenient to implement while Eq. (10) is more accurate. As pointed out in [80, 81], Hamiltonian elements change approximately linearly within 0.2–0.5 fs. Thus, with the $\Delta t < 0.05$ fs, $\frac{1}{2}H_{\mathbf{k}}(t_2) + \frac{1}{2}H_{\mathbf{k}}(t_1)$ is a better evaluation of $H(t')$ than $H_{\mathbf{k}}(t_2)$. In practice, these two scenarios yield almost the same results.

Note that, $|u_{n\mathbf{k}}(\mathbf{r})(t_2)\rangle$ is not explicitly dependent on the other TDKS orbitals $|u_{n'\mathbf{k}'}(\mathbf{r})(t_1)\rangle$ ($n' \neq n$ or $\mathbf{k}' \neq \mathbf{k}$), which is the v -representativity of the TDKS equation [82, 83]. It decouples the evolution equations of different TDKS orbitals and make the TDDFT calculation practically possible. However, it still includes the interband scattering. Because $H_{\mathbf{k}}$ is determined by the charge density, which is a weighted summation of all the

occupied orbitals, there still exists a coupling between the orbitals.

Numerally, propagator $\exp(-iS_{\mathbf{k}}^{-1}H_{\mathbf{k}}\Delta t)$ in Eq. (8) is expanded using first-order Crank-Nicholson scheme:

$$|u_{n\mathbf{k}}(\mathbf{r}, t_2)\rangle = \frac{1 - iS_{\mathbf{k}}^{-1}H_{\mathbf{k}}\Delta t/2}{1 + iS_{\mathbf{k}}^{-1}H_{\mathbf{k}}\Delta t/2} |u_{n\mathbf{k}}(\mathbf{r}, t_1)\rangle. \quad (11)$$

Technically, calculation of Eq. (11) is accelerated in two aspects: Firstly, ScaLAPACK is used for the parallel matrix inversion and multiplication. Secondly, since computing $S_{\mathbf{k}}^{-1}$ is most time-consuming part, we minimize the times of its computing. $S_{\mathbf{k}}^{-1}$ is only updated when NAO positions $\mathbf{b}_i$ are changed. Thus, when ions are fixed, $S_{\mathbf{k}}^{-1}$ is computed only once at the first ionic step. Even with ions moving, $S_{\mathbf{k}}^{-1}(t_2)$ only need to be updated once for each ionic step.

C. Update Charge density

With $|u_{n\mathbf{k}}(\mathbf{r}, t_2)\rangle$ solved in Eq. (8), the density matrix (DM) $\rho_{i\alpha, j\beta}(t_2)$ is computed accordingly as:

$$\begin{aligned} \rho_{i\alpha, j\beta}(t_2) &= \sum_n \sum_{\mathbf{k}} q_{n, \mathbf{k}} |u_{n\mathbf{k}}(\mathbf{r}, t_2)\rangle \langle u_{n\mathbf{k}}(\mathbf{r}, t_2)| \\ &= \sum_n \sum_{\mathbf{k}} q_{n, \mathbf{k}} c_{n, i\alpha, \mathbf{k}}^*(t_2) c_{n, j\beta, \mathbf{k}}(t_2), \end{aligned} \quad (12)$$

where $q_{n, \mathbf{k}}$ is the electronic population of the band n at $\mathbf{k}$, and $c_{n, j\beta, \mathbf{k}}(t_2)$ is the coefficient of $|u_{n\mathbf{k}}(\mathbf{r}, t_2)\rangle$ in NAO basis:

$$|u_{n\mathbf{k}}(\mathbf{r}, t_2)\rangle = \sum_{j\beta} c_{n, j\beta, \mathbf{k}}(t_2) \xi_{j\beta}(\mathbf{r}). \quad (13)$$

D. Self-Consistence Test

We use the self-consistence process described in Ref. [70]. This process substantially increases the numerical stability [84]. All the criteria for convergence test developed in SIESTA are compatible, such as the maximum element of the DM difference, the energy difference, the Harris energy difference etc [71].

Here, we use DM difference as an example, convergence is reached when

$$\max \{ |\rho_{i\alpha, j\beta}^{new} - \rho_{i\alpha, j\beta}| \} < \eta \quad (14)$$

where η is about 10^{-4} .

E. Mixing

If not converged, the linear mixing of DM is needed to generate the input DM for the next cycle ρ_{next} , instead of using ρ_{new} directly:

$$\rho = (1 - w)\rho + w\rho_{new}, \quad (15)$$

where the ρ is the input DM and ρ_{new} is the output DM, w is the mixing weight, usually $w = 0.1 - 0.5$.

F. Postprocesses

If self-consistence process is converged, the post-processes are evoked, such as the calculations of total energy, Hellmann-Feynman forces, ionic movements. These functions are implemented in SIESTA [71] and compatibly used in TDAP [70]. Here we only introduce some unique analysis, among which an important one is the state-to-state transition probabilities [85]:

$$P_{nn'\mathbf{k}} = |C_{nn'\mathbf{k}}|^2 = |\langle v_{n\mathbf{k}} | S_{\mathbf{k}} | u_{n'\mathbf{k}} \rangle|^2, \quad (16)$$

where $|v_{n\mathbf{k}}\rangle$ is the adiabatic basis

$$H_{\mathbf{k}} |v_{n\mathbf{k}}(\mathbf{r})\rangle = E_{n\mathbf{k}} S_{\mathbf{k}} |v_{n\mathbf{k}}(\mathbf{r})\rangle. \quad (17)$$

The population $\Pi_{n\mathbf{k}}$ of adiabatic state $n\mathbf{k}$ is thus projected from TDKS orbitals as:

$$\Pi_{n\mathbf{k}} = \sum_{n' \in n_{\mathbf{k}, occ}} q_{n'\mathbf{k}} P_{nn'\mathbf{k}}, \quad (18)$$

$n_{\mathbf{k}, occ}$ is occupied state at $\mathbf{k}$ point.

Technically, n loops over all adiabatic states, which has the dimension N_o , where N_o is the number of NAOs. Thus, the calculation is $N_{occ}O(N_o^2)$, where N_{occ} is the number of occupied TDKS states. This calculation is quite time consuming. Parallel computation is essential: Firstly, diagonalization of $H_{\mathbf{k}}$ in Eq. (17) is carried using ScaLAPACK and broadcast all $|v_{n\mathbf{k}}(\mathbf{r})\rangle$ to all nodes. Secondly, the occupied TDKS orbitals $|u_{n'\mathbf{k}}\rangle$ are distributed equally by all the computing nodes. Each node only evaluate Eq. (16) with local TDKS orbitals.

III. RESULTS AND DISCUSSIONS

A. $\mathbf{k}$ -resolved vs supercell

To demonstrate the $\mathbf{k}$ -resolved algorithm, we choose graphene as the model system [Fig. 2(a)]. An exotic property of graphene (also of other Dirac materials) is the linear dispersion near K point $E(\mathbf{k}) = v_F \mathbf{k}$, where v_F is the Fermi velocity which could reach 10^6 m/s. To describe all the Bloch electrons, especially near the Fermi energy, two kinds of strategies are used: $\mathbf{k}$ -resolved unit cell or Γ -only supercell. To exhibit the advantages of $\mathbf{k}$ -resolved algorithm, we compare three cases: (I) unit cell with the Monkhorst-Pack [86] $N_k \times N_k \times 1$ k point mesh, to covers important special points M , Γ and K , facilitating a line-mode analysis along $M \rightarrow \Gamma \rightarrow K \rightarrow M$ [Fig. 2(b)]; (II) $N_c \times N_c \times 1$ supercell with single Γ point and (III) $N_c \times N_c \times 1$ supercell with single K point.

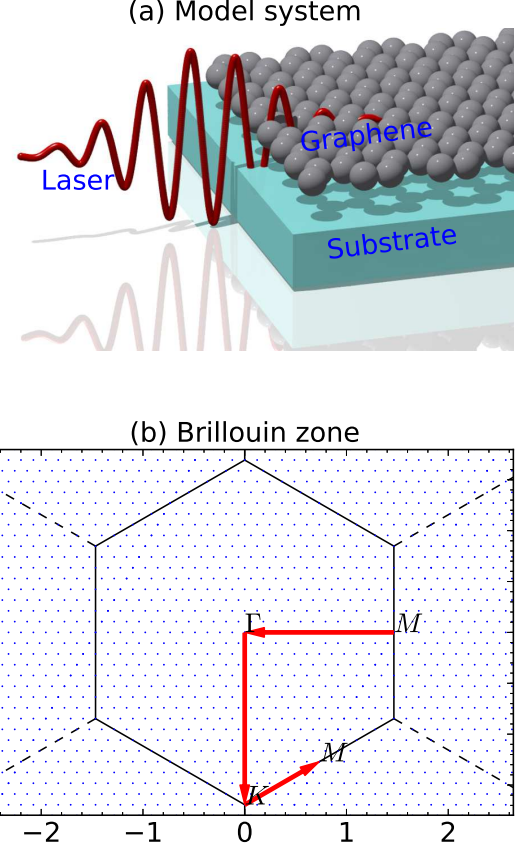


FIG. 2. (a) Diagram of the graphene with the out-of-plane polarized laser field. (b) Brillouin zone and $\mathbf{k}$ sampling of graphene. Blue dots denote the $\mathbf{k}$ points used for sampling. Red lines denote the high symmetric path.

To compare the accuracies of these three cases, we define an error function Δ as

$$\Delta = \frac{1}{T} \int_0^T |E_{ex}(t) - E_{ex}^{ref}(t)| dt \quad (19)$$

where T is the total simulation time, E_{ex}^{ref} is the excitation energy of the reference case and $E_{ex}(t)$ is excitation energy

$$E_{ex}(t) = E_{KS}(t) - E_{KS}(t=0), \quad (20)$$

where E_{KS} is Kohn-Sham energy.

Here, we evaluate Δ under such setting: the Gaussian pulse [Eq. (5)] with $\phi = 0$, $t_0 = 7.0$ fs, $\sigma = 2.0$ fs, $f = 21.93$ eV is applied; Total time is $T = 20$ fs and the reference energy E_{ex}^{ref} is calculated with $60 \times 60 \times 1$ k point mesh. Other details are listed in [87]. A diagram of Δ shown in the inset of Fig. 3. We plot Δ of these three cases in Fig. 3. The error Δ decreases as $N = N_k/N_c$ increases. Δ of the same scale is achieved with $N_c = N_k$, i.e. unit cell with $N \times N \times 1$ k point mesh is as accurate as $N \times N \times 1$ supercell. To achieve a accuracy result

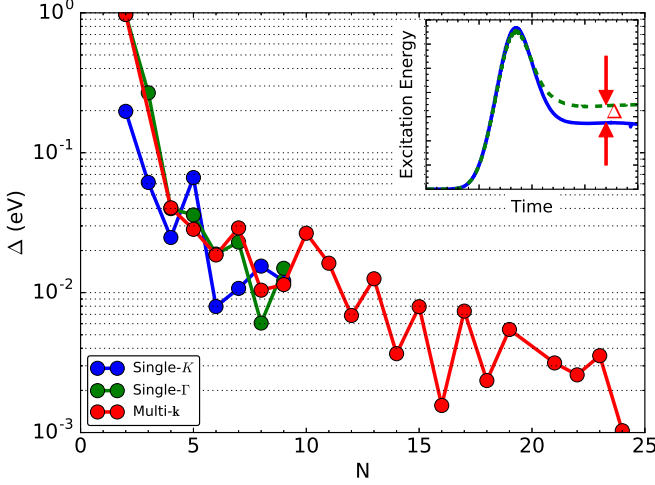


FIG. 3. Error function Δ as a function of N , as defined in Eq. (19). Different supercell and K mesh. N denotes N_k for k -resolved, N_c for single K and single Γ .

with $\Delta \leq 2$ meV, $N_k = 24$ is needed. Thus, it can be predicted that $N_C = 24$ is needed for supercell case.

However, computationally, calculation of $N_c \times N_c \times 1$ supercell is extremely heavy. As shown in Fig. 4, solving Eq. (8) dominates ($\sim 80\%$) the time consumption at large N_k (N_c), which scales linearly with the total number of k points N_k^2 and squarely with the total number of atoms N_c^2 . The CPU clock time t_c approximately scales as $O(N_k^2 \times N_c^4)$. Thus, $t_c = N_c^4$ for supercell calculation, while $t_c = N_k^2$ for the same accuracy level k -resolved calculation. As N increases, this difference become significant. For supercell case, we only calculate up to $N_C = 9$, which already costs over 2×10^3 min. At the same accuracy level, $N_k = 9$ calculation costs only 20 min, which is only 1/100 of that of $N_C = 9$ case, consistent with the time complexity analysis $N_k^2/N_c^4 = 1/81$. As mentioned before, $N_k = 24$ or $N_C = 24$ is needed for relatively accurate calculation. Fulfilling this requirement, $N_k = 24$ calculation costs about 1 hour, showing that it is accessible and efficient. In contrast, $N_c = 24$ calculation is estimated to cost over 576 hours and thus nearly impossible in application. Regarding the computational accuracy and efficiency, we choose k point mesh $24 \times 24 \times 1$ to sample the Brillouin zone.

B. Dielectric Function

We first calculate dielectric function $\alpha_{\mu,\nu}$ to locate the resonant photon energy, where μ, ν denote the spatial direction x, y, z . $\alpha_{\mu,\nu}$ is the response of dipole momentum $P_\mu(\omega)$ to the electric field $E_\nu(\omega)$ in frequency domain

$$P_\mu(\omega) = \alpha_{\mu,\nu}(\omega) E_\nu(\omega) \quad (21)$$

In rt-TDDFT calculations, we apply the electric field $E_\nu(t)$ and obtain the dipole momentum $P_\mu(t)$ in time

domain. So we carry the Fourier transform to Eq. [21]

$$\int P_\mu(t) \exp(i\omega t) dt = \alpha_{\mu,\nu}(\omega) \int E_\nu(t) \exp(i\omega t) dt \quad (22)$$

and obtain

$$\alpha_{\mu,\nu}(\omega) = \frac{\int P_\mu(t) \exp(i\omega t) dt}{\int E_\nu(t) \exp(i\omega t) dt} \quad (23)$$

$E_\nu(t)$ can be arbitrary shape in time. However, in practice, it is better to choose Dirac function $E_\nu^\delta(t) = E_{\nu 0} \delta(t)$ or Heaviside step function $E_\nu^\theta(t) = E_{\nu 0} [1 - \theta(t)]$ to contain components $E_\nu(\omega)$ at all ω , since

$$E_\nu^\delta(\omega) = \int E_{\nu 0} \delta(t) \exp(i\omega t) dt = E_{\nu 0} \quad (24)$$

$$E_\nu^\theta(\omega) = \int E_{\nu 0} [1 - \theta(t)] \exp(i\omega t) dt = \frac{E_{\nu 0}}{i\omega} \quad (25)$$

Here we choose the latter form:

$$E_\nu^\theta(t) = E_{\nu 0} [1 - \theta(t)] = \begin{cases} E_{\nu 0} & t \leq 0, \\ 0 & t > 0. \end{cases} \quad (26)$$

which leads to

$$\alpha_{\mu,\nu}(\omega) = \frac{i\omega}{E_{\nu 0}} \int P_\mu(t) \exp(i\omega t) dt \quad (27)$$

Importantly, $\text{Im}\{\alpha_{\mu,\mu}(\omega)\}$ characterizes the absorption at ω along the μ direction.

We calculate the imaginary part of the dielectric function along z direction $\text{Im}\{\alpha_{z,z}(\omega)\}$. As shown in Fig. 5, $\text{Im}\{\alpha_{z,z}(\omega)\}$ are almost the same with the increase of E^0 from 0.05 to 0.5 V/Å. The absorption peaks locate at relative high energies (> 20 eV). The first absorption peak locates at 21.93 eV. We choose this energy as the resonant photon source.

C. Absorptions at Different Light Frequencies

With the dielectric function, we demonstrate absorption dynamics of a resonant light frequency at $\omega_r = 21.93$ eV, compared with the non-resonant light frequency at $\omega_{nr} = 2.0$ eV. We characterize the overall excitation through tracking total excited electrons and excitation energy as a function of time. Excited electrons $n(t)$ is

$$n(t) = \sum_{unocc} \Pi_{n\mathbf{k}}(t) \quad (28)$$

where with $unocc$ is the unoccupied states, $\Pi_{n\mathbf{k}}(t)$ obtained from Eq. (18).

As shown in Fig. 6, total different behaviors are observed for these two cases. The excited electrons $n(t)$ and excitation energy $E_{ex}(t)$ increases at ω_r , while no response is observed at ω_{nr} . Same results are obtained

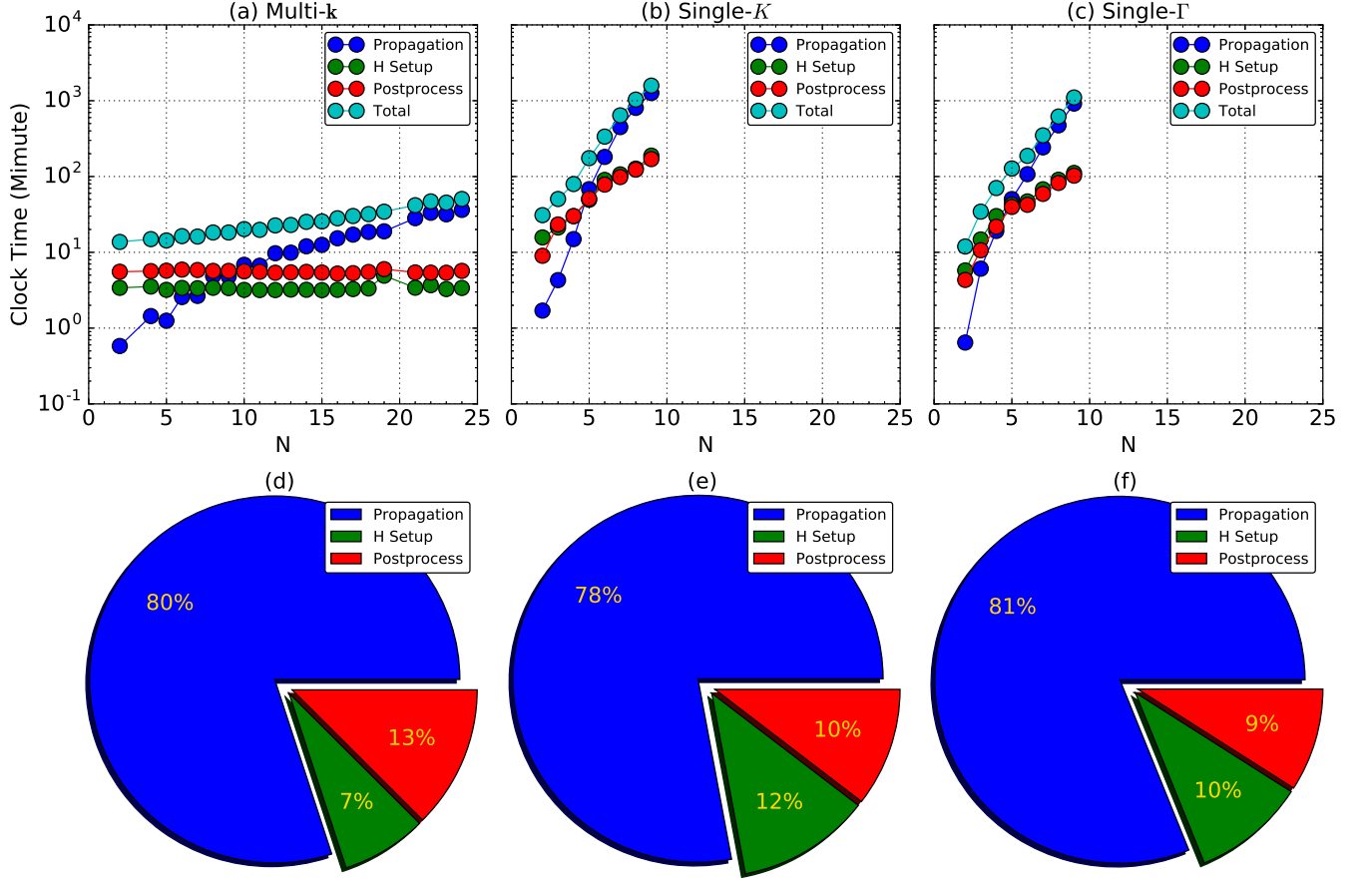


FIG. 4. (a) – (c) CPU clock time as a function of N_k or N_c . *H setup* corresponds to Eq. (3), *Postprocesses* mainly contains the calculation of Hellmann-Feynman forces, and *Propagation* corresponds to Eq (8). (d) – (f) Percentages of the time consumption of each processes with (d) $N_k = 24$, (e)(f) $N_c = 9$.

at other non-resonant light frequencies of 1.0, 2.0, 4.0 eV. It verifies that calculated $\text{Im}\{\alpha_{z,z}(\omega)\}$ characterized the absorption selection correctly.

We focus on the resonate case. Generally, $n(t)$ is similar to the shape of the laser pulse, while two special features are observed. Firstly, the variation of $n(t)$ has a 1.4 fs delay from the laser field. This delay represents the intrinsic response time of graphene, i.e. the absorption time. Secondly, residual $n(t)$ sustain after the laser pulse vanishes. Thus, we assume that two kinds of excitation exist: one is the transient excited electrons, which quickly vanishes after the laser is off; another one is the residual excited electrons, which live relatively longer. Residual $n(t)$ decrease with the electron-electron and further electron-phonon scattering at the time scale of 100 fs, thus not observed in our simulation (< 20 fs).

D. K Resolved Excitation Behavior

To verify our assumption about the existence of two kinds of excitations, we further distinguish the excitations with $\mathbf{k}$ resolution. We choose six snapshots of

$\Pi_{n\mathbf{k}}(t)$ in Eq. (18) shown in Fig. 7. At $t = 2.0$ fs when laser pulse is still off, no excitation is observed at all $\mathbf{k}$ points. At $t = 4.0$ fs, the excitation is still ignorable, while the laser field is on, due to the response delay we discussed before. At the peak time of the laser pulse $t = 7.0$ fs, $\Pi_{n\mathbf{k}}(t)$ shows a large distributions. We mark the dominant excitation mode as L, which evolving bonding π and antibonding π bands. With t increases from 7 fs to 12 fs, the L mode excitation rapidly decreases. In contrast, two new modes (labeled with their locations K_1 and K_2) increases and become dominant. K_1 and K_2 modes maintain within 20 fs while L mode totally vanishes. Thus, with the assistance of new developed $\mathbf{k}$ -resolved algorithm, we distinguish these two kinds of excitations: L mode produce the transient excited electrons while K_1 and K_2 modes produce to the residual excited electrons.

Although K_1 and K_2 are both long lived excitations, their time-dependences are different. We plot $\Pi_{n\mathbf{k}}(t)$ as a function of t at three $\mathbf{k}$ points Γ , K_1 and K_2 , as shown in Fig. 8. For L mode (represented by Γ point), the clear transient character is demonstrated. The excitation only exists with the laser pulse, which is consistent with

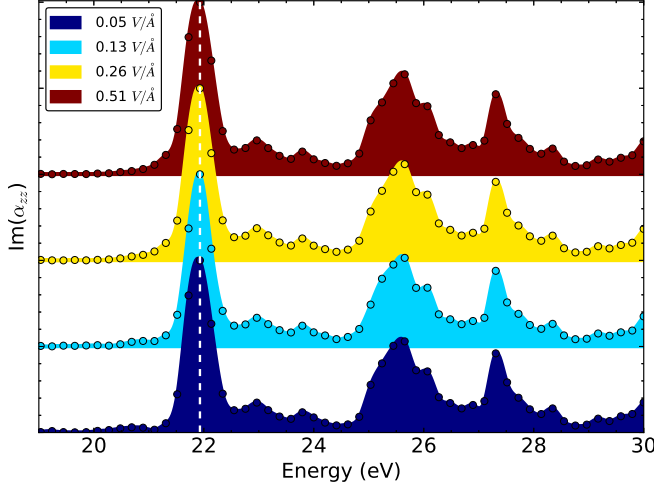


FIG. 5. $\text{Im}\{\alpha_{\mu,\mu}(\omega)\}$ as a function of photon energy ω at different E_z^0 using Eq. (27).

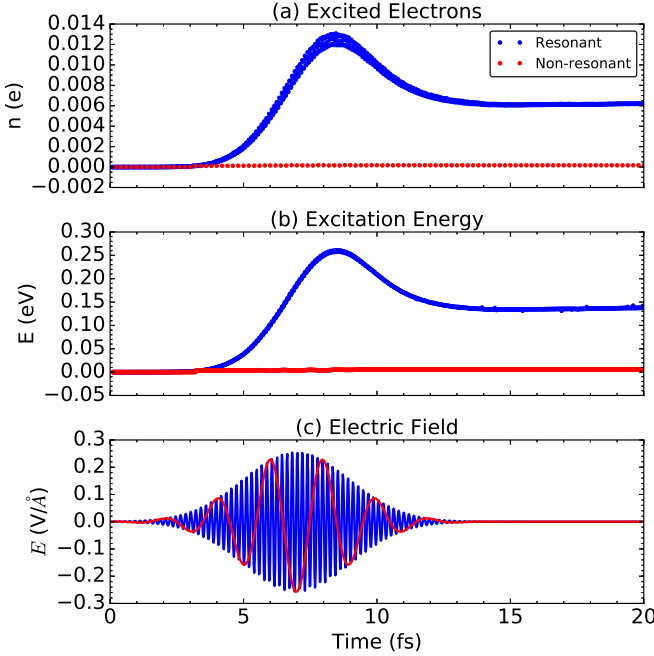


FIG. 6. (a) Excited electrons, (b) excitation energy and (c) electric field as a function of time. Blue curves are non-resonant case at the $\omega_{nr} = 2.0$ eV while red curves are resonant case at the $\omega_r = 21.93$ eV.

the observation from Fig. 7. However, for K_1 and K_2 modes, new difference is observed. Excited electrons in K_1 mode increases monotonically, while $\Pi_{n\mathbf{k}}(t)$ at K_2 shows a oscillation with periodicity $T_{K_2} \sim 5$ fs. These different behaviors are due to different exciton energies of three modes. The oscillation of K_2 mode is analogue

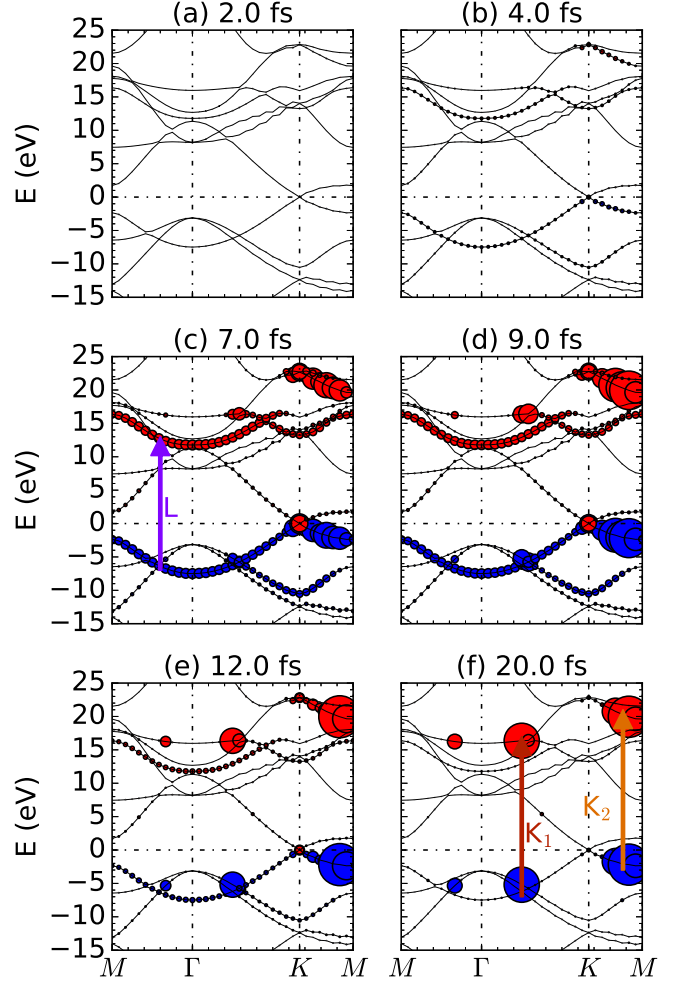


FIG. 7. Snapshots of excitation $\Delta\Pi_{n\mathbf{k}}(t)$ at different time t . Black curves are the band structures. Blue cycles represent $\Delta\Pi_{n\mathbf{k}}(t) < 0$ and red cycles represent $\Delta\Pi_{n\mathbf{k}}(t) > 0$. Radius of cycles are proportional to $|\Delta\Pi_{n\mathbf{k}}(t)|$.

to the wave beat:

$$\Pi_{nK_1}(t) = A_0 \cos\left(\frac{\omega_{K_2} - \omega_r}{2}t\right) \cos\left(\frac{\omega_{K_2} + \omega_r}{2}t\right). \quad (29)$$

For K_2 mode, $\omega_{K_2} = 22.75$ eV is the energy difference between excitation outgoing and ingoing state and $\omega_2 = \omega_r = 21.93$ eV is the photon energy. Beat frequency $T_b = 4\pi/(\omega_1 - \omega_2) = 5.07$ fs, which is close to the oscillation periodicity T_{K_2} . Thus, the oscillation of K_2 mode is the beat formed by the intrinsic band energy difference and the driven laser frequency. In contrast, K_1 mode exciton has the closest energy $\omega_{K_1} = 21.59$ eV to $\omega_r = 21.93$ eV, thus only half period of the beat ($T_{K_1} = 12.4$ fs) is observed in our simulation. For L mode, the exciton energy is 19.32 eV, far below the ω_r . A non-resonant interference is formed instead of a beat.

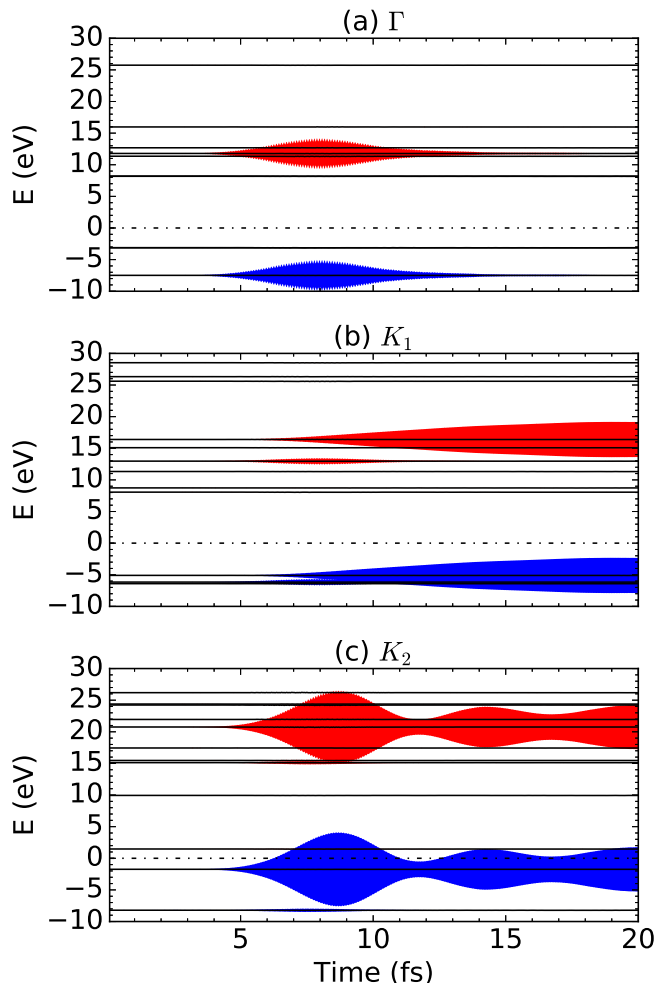


FIG. 8. Excitation $\Delta\Pi_{nk}(t)$ at different $\mathbf{k}$ as a function of time. Blue lines represent $\Delta\Pi_{nk}(t) < 0$ and red lines represent $\Delta\Pi_{nk}(t) > 0$ in population. Widths of the lines are proportional to $|\Delta\Pi_{nk}(t)|$.

IV. CONCLUSIONS

In conclusion, we have developed the $\mathbf{k}$ -resolved rt-TDDFT algorithm. It enable rt-TDDFT calculation of solid using unit cell and reduce largely computational cost. Moreover, $\mathbf{k}$ resolved excitation dynamics are observed. Applied on graphene, we observed $\mathbf{k}$ selective excitation. Three modes are excited, located at different $\mathbf{k}$. This kind of $\mathbf{k}$ dependent electronic dynamics are ubiquitous in solids. Thus, $\mathbf{k}$ -resolved rt-TDDFT algorithm is important and will be widely used.

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